

# Schmitt Trigger Buffer, Dual, Non-Inverting

## NL27WZ17

The NL27WZ17 is a high performance dual buffer with Schmitt-Trigger inputs operating from a 1.65 to 5.5 V supply.

### Features

- Designed for 1.65 V to 5.5 V  $V_{CC}$  Operation
- 3.7 ns  $t_{PD}$  at  $V_{CC} = 5$  V (Typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- $I_{OFF}$  Supports Partial Power Down Protection
- Sink 32 mA at 4.5 V
- Available in SC-88, SC-74, and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

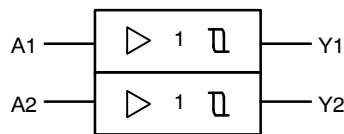

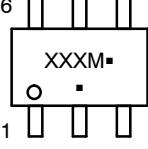

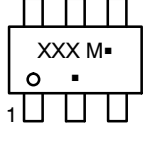






Figure 1. Logic Symbol



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MARKING DIAGRAMS		
	<b>SC-88 DF SUFFIX CASE 419B-02</b>	
	<b>SC-74 CASE 318F-05</b>	
	<b>UDFN6 1.45x1.0, 0.5P CASE 517AQ</b>	
	<b>UDFN6 1x1, 0.35P CASE 517BX</b>	

X, XXX = Specific Device Code

M = Date Code\*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

# NL27WZ17

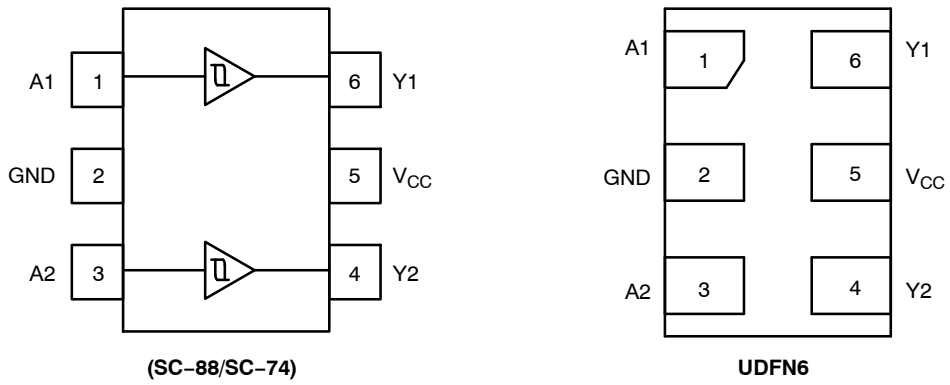


Figure 2. Pinout (Top View)

## PIN ASSIGNMENT

Pin	Function
1	A1
2	GND
3	A2
4	Y2
5	V <sub>CC</sub>
6	Y1

## FUNCTION TABLE

A Input	Y Output
L	L
H	H

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## MAXIMUM RATINGS

Symbol	Characteristics	Value	Units
V <sub>CC</sub>	DC Supply Voltage SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V <sub>IN</sub>	DC Input Voltage SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V <sub>OUT</sub>	DC Output Voltage SC-88 (NLV) Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V <sub>CC</sub> = 0 V)	-0.5 to V <sub>CC</sub> +0.5 -0.5 to +7.0 -0.5 to +7.0	V
	DC Output Voltage SC-88, SC-74, UDFN6 Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V <sub>CC</sub> = 0 V)	-0.5 to V <sub>CC</sub> +0.5 -0.5 to +6.5 -0.5 to +6.5	V
I <sub>IK</sub>	DC Input Diode Current, V <sub>IN</sub> < GND	-50	mA
I <sub>OK</sub>	DC Output Diode Current, V <sub>OUT</sub> < GND	-50	mA
I <sub>OUT</sub>	DC Output Source/Sink Current	±50	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC Supply Current per Supply Pin or Ground Pin	±100	mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 secs	260	°C
T <sub>J</sub>	Junction Temperature under Bias	+150	°C
θ <sub>JA</sub>	Thermal Resistance (Note 2) SC-88 SC-74 UDFN6	377 320 154	°C/W
P <sub>D</sub>	Power Dissipation in Still Air SC-88 SC-74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity	Level 1	-
F <sub>R</sub>	Flameability Rating Oxygen Index: 28 to 34	UL 94-V-0 @ 0.125 in	-
V <sub>ESD</sub>	ESD Withstand Voltage (Note 3) Human Body Model Charged Device Model (NLV) Charged Device Model	2000 1000 N/A	V
I <sub>LATCHUP</sub>	Latchup Performance (Note 4) (NLV)	±100 ±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage	1.65	5.5	V
V <sub>IN</sub>	DC Input Voltage	0	5.5	V
V <sub>OUT</sub>	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V <sub>CC</sub> = 0 V)	0	V <sub>CC</sub>	V
		0	5.5	
		0	5.5	
T <sub>A</sub>	Operating Temperature Range	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Transition Rise or Fall Rate V <sub>CC</sub> = 1.65 V to 1.95 V V <sub>CC</sub> = 2.3 V to 2.7 V V <sub>CC</sub> = 3.0 V to 3.6 V V <sub>CC</sub> = 4.5 V to 5.5 V	0	No Limit	ns
		0	No Limit	
		0	No Limit	
		0	No Limit	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

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## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			-40°C ≤ T <sub>A</sub> ≤ 85°C		-55°C ≤ T <sub>A</sub> ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V <sub>T+</sub>	Positive Input Threshold Voltage		1.65	-	1.0	1.4	-	1.4	-	1.4	V
			2.3	-	1.5	1.8	-	1.8	-	1.8	
			2.7	-	1.7	2	-	2	-	2	
			3	-	1.9	2.2	-	2.2	-	2.2	
			4.5	-	2.7	3.1	-	3.1	-	3.1	
			5.5	-	3.3	3.6	-	3.6	-	3.6	
V <sub>T-</sub>	Negative Input Threshold Voltage		1.65	0.2	0.5	-	0.2	-	0.2	-	V
			2.3	0.4	0.75	-	0.4	-	0.4	-	
			2.7	0.5	0.87	-	0.5	-	0.5	-	
			3	0.6	1.0	-	0.6	-	0.6	-	
			4.5	1.0	1.5	-	1.0	-	1.0	-	
			5.5	1.2	1.9	-	1.2	-	1.2	-	
V <sub>H</sub>	Input Hysteresis Voltage		1.65	0.1	0.48	0.9	0.1	0.9	0.1	0.9	V
			2.3	0.25	0.75	1.1	0.25	1.1	0.25	1.1	
			2.7	0.3	0.83	1.15	0.3	1.15	0.3	1.15	
			3	0.4	0.93	1.2	0.4	1.2	0.4	1.2	
			4.5	0.6	1.2	1.5	0.6	1.5	0.6	1.5	
			5.5	0.7	1.4	1.7	0.7	1.7	0.7	1.7	
V <sub>OH</sub>	High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -100 μA	1.65 to 5.5	V <sub>CC</sub> - 0.1	V <sub>CC</sub>	-	V <sub>CC</sub> - 0.1	-	V <sub>CC</sub> - 0.1	-	V
		I <sub>OH</sub> = -4 mA	1.65	1.29	1.52	-	1.29	-	1.29	-	
		I <sub>OH</sub> = -8 mA	2.3	1.9	2.1	-	1.9	-	1.9	-	
		I <sub>OH</sub> = -12 mA	2.7	2.2	2.4	-	2.2	-	2.2	-	
		I <sub>OH</sub> = -16 mA	3	2.4	2.7	-	2.4	-	2.4	-	
		I <sub>OH</sub> = -24 mA	3	2.3	2.5	-	2.3	-	2.3	-	
		I <sub>OH</sub> = -32 mA	4.5	3.8	4	-	3.8	-	3.8	-	
V <sub>OL</sub>	Low-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 100 μA	1.65 to 5.5	-	-	0.1	-	0.1	-	0.1	V
		I <sub>OL</sub> = 4 mA	1.65	-	0.08	0.24	-	0.24	-	0.24	
		I <sub>OL</sub> = 8 mA	2.3	-	0.2	0.3	-	0.3	-	0.3	
		I <sub>OL</sub> = 12 mA	2.7	-	0.22	0.4	-	0.4	-	0.4	
		I <sub>OL</sub> = 16 mA	3	-	0.28	0.4	-	0.4	-	0.4	
		I <sub>OL</sub> = 24 mA	3	-	0.38	0.55	-	0.55	-	0.55	
		I <sub>OL</sub> = 32 mA	4.5	-	0.42	0.55	-	0.55	-	0.55	
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	1.65 to 5.5	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V	0	-	-	1	-	10	-	10	μA
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = 5.5 V or GND	5.5	-	-	1	-	10	-	10	μA

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## AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			-40°C ≤ T <sub>A</sub> ≤ 85°C		-55°C ≤ T <sub>A</sub> ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, A to Y (Figures 3 and 4)	R <sub>L</sub> = 1 MΩ, C <sub>L</sub> = 15 pF	1.65 to 1.95	–	9.1	15	–	15.6	–	15.6	ns
			2.3 to 2.7	–	5.0	9.0	–	9.5	–	9.5	
		R <sub>L</sub> = 1 MΩ, C <sub>L</sub> = 15 pF	3.0 to 3.6	–	3.7	6.3	–	6.5	–	6.5	
			4.5 to 5.5	–	3.1	5.2	–	5.5	–	5.5	
			R <sub>L</sub> = 500 Ω, C <sub>L</sub> = 50 pF	3.0 to 3.6	–	4.4	7.2	–	7.5	–	
		4.5 to 5.5		–	3.7	5.9	–	6.2	–	6.2	

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>CC</sub> = 5.5 V, V <sub>I</sub> = 0 V or V <sub>CC</sub>	2.5	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>CC</sub> = 5.5 V, V <sub>I</sub> = 0 V or V <sub>CC</sub>	4.0	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 5)	10 MHz, V <sub>CC</sub> = 3.3 V, V <sub>IN</sub> = 0 V or V <sub>CC</sub> 10 MHz, V <sub>CC</sub> = 5.0 V, V <sub>IN</sub> = 0 V or V <sub>CC</sub>	11 12.5	pF

5. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} \cdot I_{CC}$ . C<sub>PD</sub> is used to determine the no-load dynamic power consumption;  $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} \cdot I_{CC} \cdot V_{CC}$ .

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$C_L$  includes probe and jig capacitance  
 $R_T$  is  $Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )  
 $f = 1$  MHz

**Figure 3. Test Circuit**

Test	Switch Position	$C_L$ , pF	$R_L$ , $\Omega$	$R_1$ , $\Omega$
$t_{PLH} / t_{PHL}$	Open	See AC Characteristics Table		
$t_{PLZ} / t_{PZL}$	$2 \times V_{CC}$	-	-	-
		See AC Characteristics Table		
$t_{PHZ} / t_{PZH}$	GND	-	-	-
		See AC Characteristics Table		

X = Don't Care



**Figure 4. Switching Waveforms**

$V_{CC}$ , V	$V_{mi}$ , V	$V_{mo}$ , V		$V_Y$ , V
		$t_{PLH}$ , $t_{PHL}$	$t_{PZL}$ , $t_{PLZ}$ , $t_{PZH}$ , $t_{PHZ}$	
1.65 to 1.95	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.15
2.3 to 2.7	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.15
3.0 to 3.6	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.3
4.5 to 5.5	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	0.3

# NL27WZ17

## ORDERING INFORMATION

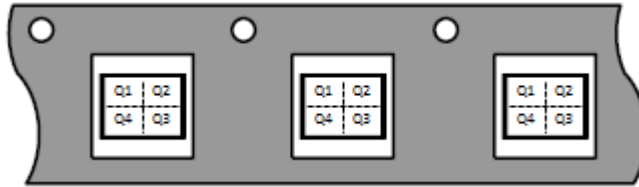
Device	Package	Specific Device Code	Pin1 Orientation (See below)	Shipping†
NL27WZ17DFT2G	SC-88	MX	Q4	3000 / Tape & Reel
NLV27WZ17DFT2G*	SC-88	MX	Q4	3000 / Tape & Reel
NL27WZ17DBVT1G	SC-74	AC	Q4	3000 / Tape & Reel
NL27WZ17MU1TCG	UDFN6 1.45 x 1.0, 0.5P	K (Rotated 90° CW)	Q4	3000 / Tape & Reel
NL27WZ17MU3TCG	UDFN6 1.0 x 1.0, 0.35P	D	Q4	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

### Pin 1 Orientation in Tape and Reel

Direction of Feed



# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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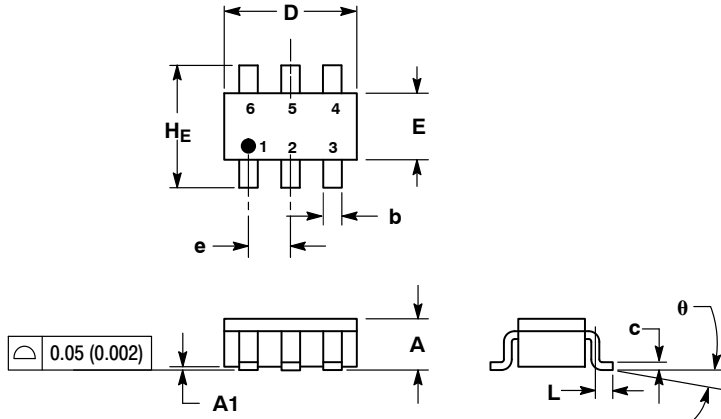


### SC-74 CASE 318F-05 ISSUE N

DATE 08 JUN 2012



SCALE 2:1

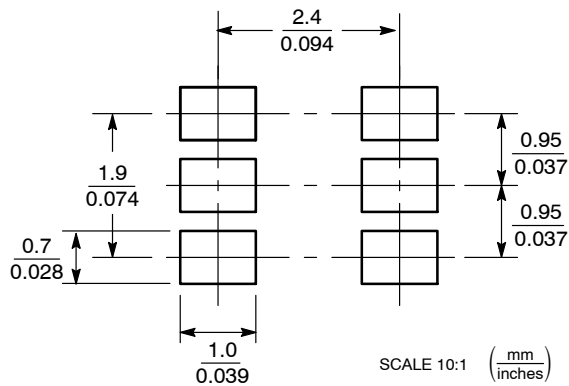


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

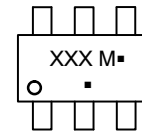
DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

**SOLDERING FOOTPRINT\***



SCALE 10:1 (mm/inches)

**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- |  |   |  |   |  |  |
|--|---|--|---|--|--|
| <p><b>STYLE 1:</b><br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. ANODE<br/>6. CATHODE</p>     | <p><b>STYLE 2:</b><br/>PIN 1. NO CONNECTION<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. NO CONNECTION<br/>5. COLLECTOR<br/>6. BASE</p> | <p><b>STYLE 3:</b><br/>PIN 1. EMITTER 1<br/>2. BASE 1<br/>3. COLLECTOR 2<br/>4. EMITTER 2<br/>5. BASE 2<br/>6. COLLECTOR 1</p> | <p><b>STYLE 4:</b><br/>PIN 1. COLLECTOR 2<br/>2. EMITTER 1/EMITTER 2<br/>3. COLLECTOR 1<br/>4. EMITTER 3<br/>5. BASE 1/BASE 2/COLLECTOR 3<br/>6. BASE 3</p> | <p><b>STYLE 5:</b><br/>PIN 1. CHANNEL 1<br/>2. ANODE<br/>3. CHANNEL 2<br/>4. CHANNEL 3<br/>5. CATHODE<br/>6. CHANNEL 4</p> | <p><b>STYLE 6:</b><br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. CATHODE<br/>6. CATHODE</p> |
| <p><b>STYLE 7:</b><br/>PIN 1. SOURCE 1<br/>2. GATE 1<br/>3. DRAIN 2<br/>4. SOURCE 2<br/>5. GATE 2<br/>6. DRAIN 1</p> | <p><b>STYLE 8:</b><br/>PIN 1. EMITTER 1<br/>2. BASE 2<br/>3. COLLECTOR 2<br/>4. EMITTER 2<br/>5. BASE 1<br/>6. COLLECTOR 1</p>    | <p><b>STYLE 9:</b><br/>PIN 1. EMITTER 2<br/>2. BASE 2<br/>3. COLLECTOR 1<br/>4. EMITTER 1<br/>5. BASE 1<br/>6. COLLECTOR 2</p> | <p><b>STYLE 10:</b><br/>PIN 1. ANODE/CATHODE<br/>2. BASE<br/>3. EMITTER<br/>4. COLLECTOR<br/>5. ANODE<br/>6. CATHODE</p>                                    | <p><b>STYLE 11:</b><br/>PIN 1. EMITTER<br/>2. BASE<br/>3. ANODE/CATHODE<br/>4. ANODE<br/>5. CATHODE<br/>6. COLLECTOR</p>   |  |

<b>DOCUMENT NUMBER:</b>	<b>98ASB42973B</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SC-74</b>	<b>PAGE 1 OF 1</b>

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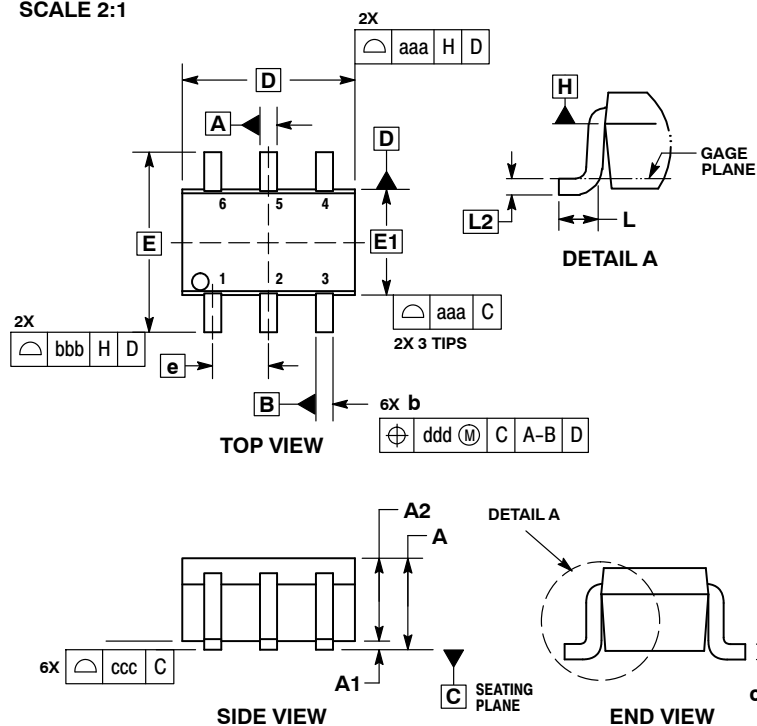




1  
 SCALE 2:1

SC-88/SC70-6/SOT-363  
 CASE 419B-02  
 ISSUE Y

DATE 11 DEC 2012



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
  4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
  5. DATUMS A AND B ARE DETERMINED AT DATUM H.
  6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
  7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
 M = Date Code\*  
 ▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

**RECOMMENDED SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**STYLES ON PAGE 2**

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**SC-88/SC70-6/SOT-363**  
**CASE 419B-02**  
**ISSUE Y**

DATE 11 DEC 2012

<b>STYLE 1:</b> PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	<b>STYLE 2:</b> CANCELLED	<b>STYLE 3:</b> CANCELLED	<b>STYLE 4:</b> PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	<b>STYLE 5:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 6:</b> PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
<b>STYLE 7:</b> PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	<b>STYLE 8:</b> CANCELLED	<b>STYLE 9:</b> PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	<b>STYLE 10:</b> PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	<b>STYLE 11:</b> PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	<b>STYLE 12:</b> PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
<b>STYLE 13:</b> PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 14:</b> PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	<b>STYLE 15:</b> PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	<b>STYLE 16:</b> PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	<b>STYLE 17:</b> PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	<b>STYLE 18:</b> PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
<b>STYLE 19:</b> PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	<b>STYLE 20:</b> PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	<b>STYLE 21:</b> PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	<b>STYLE 22:</b> PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	<b>STYLE 23:</b> PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	<b>STYLE 24:</b> PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
<b>STYLE 25:</b> PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	<b>STYLE 26:</b> PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	<b>STYLE 27:</b> PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	<b>STYLE 28:</b> PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	<b>STYLE 29:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	<b>STYLE 30:</b> PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

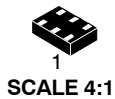
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# MECHANICAL CASE OUTLINE

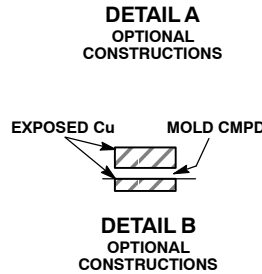
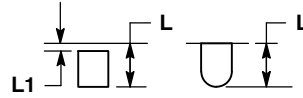
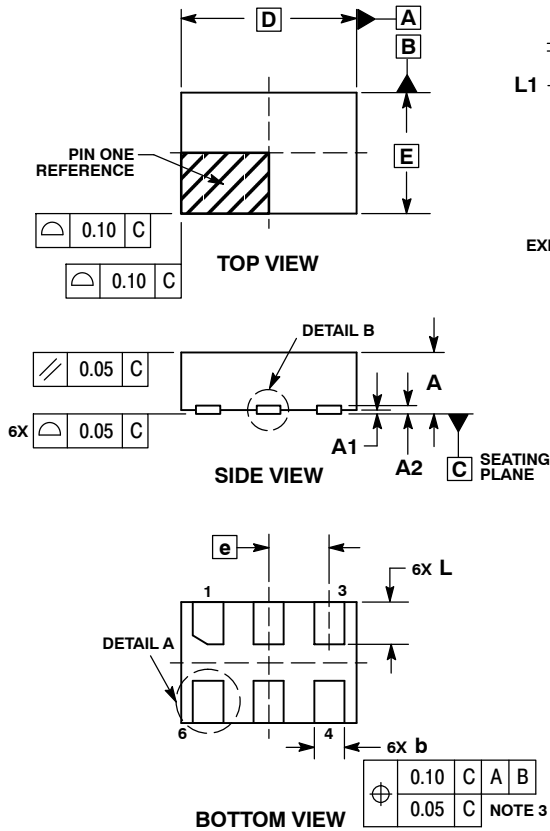
## PACKAGE DIMENSIONS

ON Semiconductor®



UDFN6, 1.45x1.0, 0.5P  
CASE 517AQ-01  
ISSUE O

DATE 15 MAY 2008



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A2	0.07	REF
b	0.20	0.30
D	1.45	BSC
E	1.00	BSC
e	0.50	BSC
L	0.30	0.40
L1	---	0.15

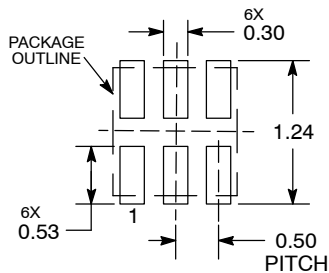
**GENERIC MARKING DIAGRAM\***



- X = Specific Device Code
- M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.

**MOUNTING FOOTPRINT**



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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<b>DESCRIPTION:</b>	UDFN6, 1.45X1.0, 0.5P	<b>PAGE 1 OF 2</b>



# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

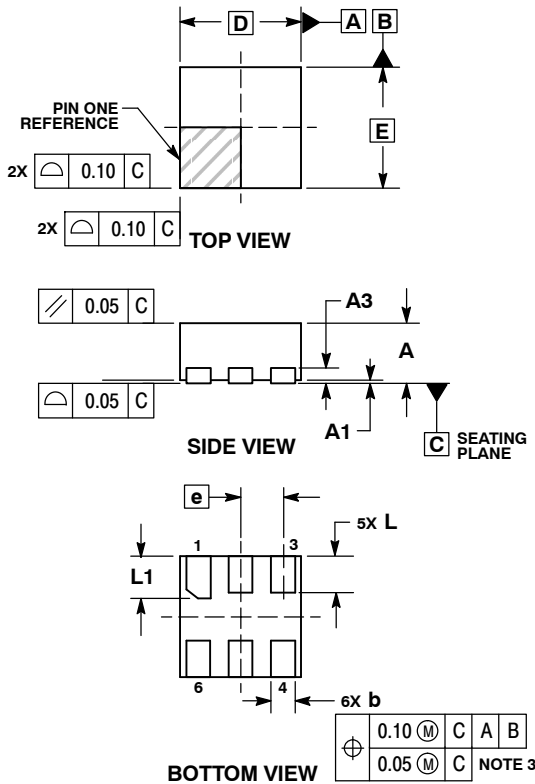
ON Semiconductor®



SCALE 4:1

UDFN6, 1x1, 0.35P  
CASE 517BX-01  
ISSUE O

DATE 18 MAY 2011

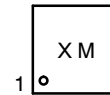


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13	REF
b	0.12	0.22
D	1.00	BSC
E	1.00	BSC
e	0.35	BSC
L	0.25	0.35
L1	0.30	0.40

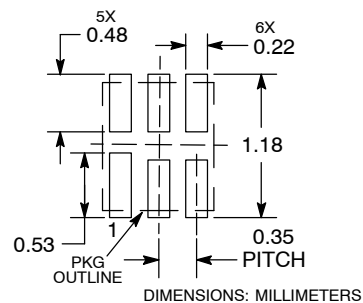
**GENERIC MARKING DIAGRAM\***



X = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**RECOMMENDED SOLDERING FOOTPRINT\***



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<b>DESCRIPTION:</b>	UDFN6, 1X1, 0.35P	<b>PAGE 1 OF 2</b>



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